

## BAS40 SERIES SCHOTTKY DIODE

### FEATURES

Power dissipation

$P_D$ : 200 mW ( $T_{amb}=25^\circ\text{C}$ )

Forward Current

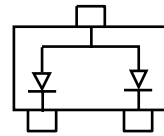
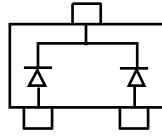
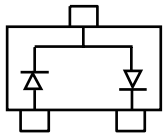
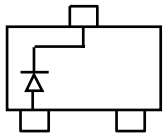
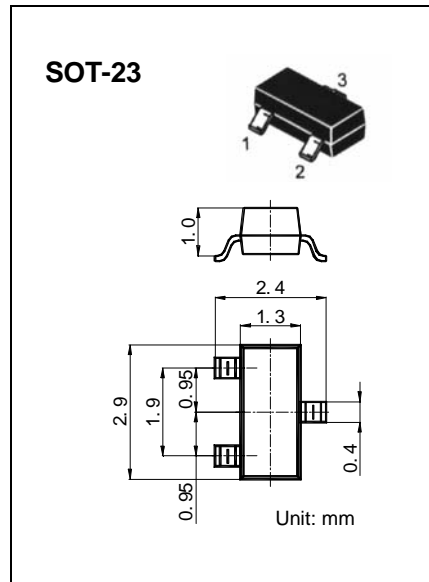
$I_F$ : 200 mA

Reverse Voltage

$V_R$ : 40 V

Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$



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### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	40		V
Reverse voltage leakage current	$I_R$	$V_R=30\text{V}$		100	nA
Forward voltage	$V_F$	$I_F=1\text{mA}$ $I_F=40\text{mA}$		380 1000	mV
Diode capacitance	$C_D$	$V_R=0\text{V}, f=1\text{MHz}$		5	pF
Reverse recovery time	$t_{rr}$	$I_F=10\text{mA}$ through $I_R=10\text{mA}$ to $I_R=1\text{mA}$		5	nS